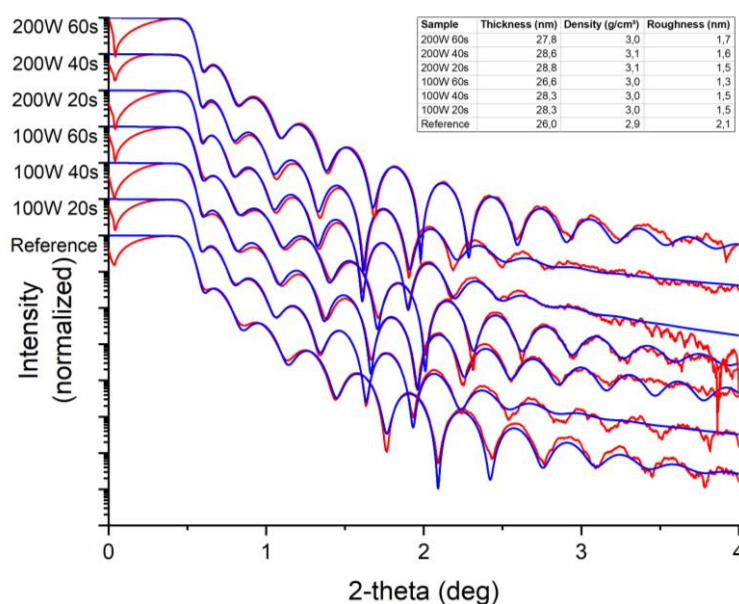


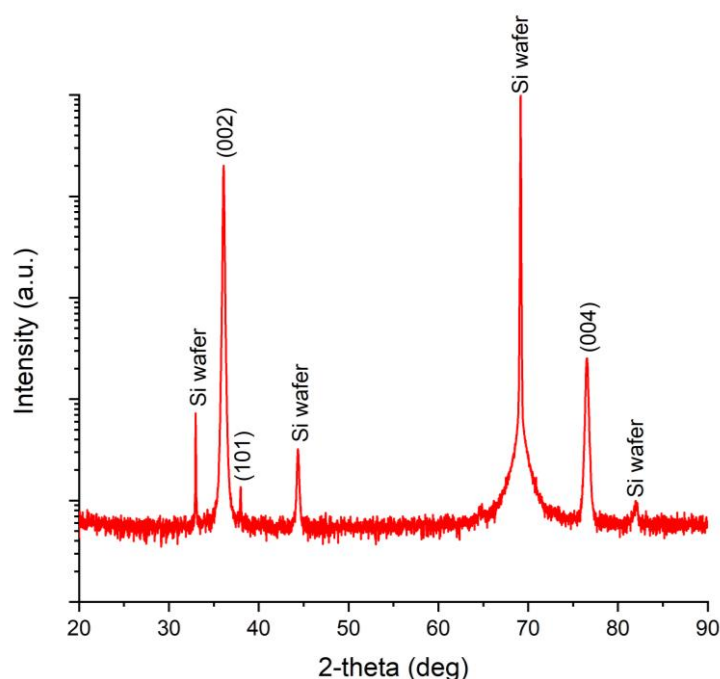
Article

# Aluminum Nitride Transition Layer for Power Electronics Applications Grown by Plasma-Enhanced Atomic Layer Deposition

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**Figure S1.** The thickness of the film is in accordance with the approximately 28nm thickness obtained from both ellipsometry and X-ray reflectometry.



**Figure S2.** The  $\theta$ - $2\theta$  XRD pattern of the regrown AlN by MOCVD on top of PEALD template.